74AUP1Z125

Low-power X-tal driver with enable and internal resistor

Rev. 02 — 7 August 2008 Product data sheet

1. General description

The 74AUP1Z125 combines the functions of the 74AUP1GU04 and 74AUP1G125 with enable circuitry and an internal bias resistor to provide a device optimized for use in crystal oscillator applications.

When not in use the $\overline{EN}$ input can be driven HIGH, pulling up the X1 input and putting the device in a low power disable mode. Schmitt trigger action at the $\overline{EN}$ input makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} at output Y. The I_{OFF} circuitry disables the output Y, preventing the damaging backflow current through the device when it is powered down.

The integration of the two devices into the 74AUP1Z125 produces the benefits of a compact footprint, lower power dissipation and stable operation over a wide range of frequency and temperature.

2. Features

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
  - HBM JESD22-A114E Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101C exceeds 1000 V
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation at output Y
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C

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3. Ordering information

Table 1. Ordering information

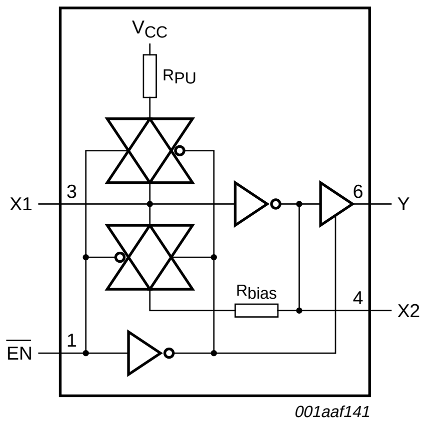
Type number	Package			
	Temperature range	Name	Description	Version
74AUP1Z125GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74AUP1Z125GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74AUP1Z125GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891

4. Marking

Table 2. Marking

Type number	Marking code
74AUP1Z125GW	55
74AUP1Z125GM	55
74AUP1Z125GF	55

5. Functional diagram



R_{PU} = pull-up resistance.

R_{bias} = bias resistance.

Fig 1. Logic symbol

6. Pinning information

6.1 Pinning

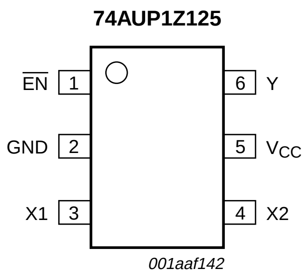


Fig 2. Pin configuration SOT363 (SC-88)

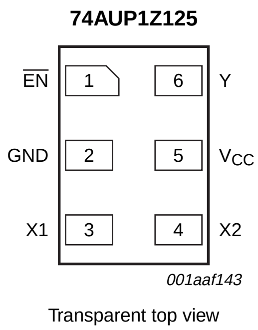


Fig 3. Pin configuration SOT886 (XSON6)

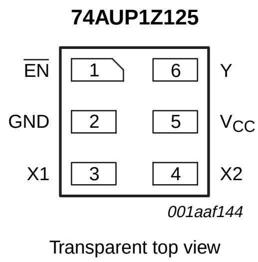


Fig 4. Pin configuration SOT891 (XSON6)

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
$\overline{EN}$	1	enable input (active LOW)
GND	2	ground (0 V)
X1	3	data input
X2	4	unbuffered output
V_{CC}	5	supply voltage
Y	6	data output

7. Functional description

Table 4. Function table[1]

Input		Output	
$\overline{EN}$	X1	X2	Y
L	L	H	H
L	H	L	L
H	L	H	Z
H	H	L	Z

[1] H = HIGH voltage level;
L = LOW voltage level;
Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V		–50	-	mA
V_I	input voltage		[1]	–0.5	+4.6	V
I_{OK}	output clamping current	$V_O < 0$ V		–50	-	mA
V_O	output voltage	Active mode and Power-down mode	[1]	–0.5	+4.6	V
I_O	output current	$V_O = 0$ V to V_{CC}		-	±20	mA
I_{CC}	supply current			-	50	mA
I_{GND}	ground current			–50	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C	[2]	-	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
For XSON6 packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
V_I	input voltage		0	3.6	V
V_O	output voltage		0	V_{CC}	V
T_{amb}	ambient temperature		–40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 0.8 V to 3.6 V	-	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V_{IH}	HIGH-level input voltage	X1 input				
		V_{CC} = 0.8 V to 3.6 V	0.75 × V_{CC}	-	-	V
		$\overline{EN}$ input				
		V_{CC} = 0.8 V	0.70 × V_{CC}	-	-	V
		V_{CC} = 0.9 V to 1.95 V	0.65 × V_{CC}	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V_{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	X1 input				
		V_{CC} = 0.8 V to 3.6 V	-	-	0.25 × V_{CC}	V
		$\overline{EN}$ input				
		V_{CC} = 0.8 V	-	-	0.30 × V_{CC}	V
		V_{CC} = 0.9 V to 1.95 V	-	-	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	Y output; V_I at X1 input = V_{IH} or V_{IL}				
		I_O = −20 µA; V_{CC} = 0.8 V to 3.6 V	V_{CC} − 0.1	-	-	V
		I_O = −1.1 mA; V_{CC} = 1.1 V	0.75 × V_{CC}	-	-	V
		I_O = −1.7 mA; V_{CC} = 1.4 V	1.11	-	-	V
		I_O = −1.9 mA; V_{CC} = 1.65 V	1.32	-	-	V
		I_O = −2.3 mA; V_{CC} = 2.3 V	2.05	-	-	V
		I_O = −3.1 mA; V_{CC} = 2.3 V	1.9	-	-	V
		I_O = −2.7 mA; V_{CC} = 3.0 V	2.72	-	-	V
		I_O = −4.0 mA; V_{CC} = 3.0 V	2.6	-	-	V
		X2 output; V_I = GND or V_{CC}				
		I_O = −20 µA; V_{CC} = 0.8 V to 3.6 V	V_{CC} − 0.1	-	-	V
		I_O = −1.1 mA; V_{CC} = 1.1 V	0.75 × V_{CC}	-	-	V
		I_O = −1.7 mA; V_{CC} = 1.4 V	1.11	-	-	V
		I_O = −1.9 mA; V_{CC} = 1.65 V	1.32	-	-	V
		I_O = −2.3 mA; V_{CC} = 2.3 V	2.05	-	-	V
		I_O = −3.1 mA; V_{CC} = 2.3 V	1.9	-	-	V
		I_O = −2.7 mA; V_{CC} = 3.0 V	2.72	-	-	V
		I_O = −4.0 mA; V_{CC} = 3.0 V	2.6	-	-	V

Table 7. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{OL}	LOW-level output voltage	Y output; V_I at X1 input = V_{IH} or V_{IL}					
		I_O = 20 μA; V_{CC} = 0.8 V to 3.6 V		-	-	0.1	V
		I_O = 1.1 mA; V_{CC} = 1.1 V		-	-	0.3 × V_{CC}	V
		I_O = 1.7 mA; V_{CC} = 1.4 V		-	-	0.31	V
		I_O = 1.9 mA; V_{CC} = 1.65 V		-	-	0.31	V
		I_O = 2.3 mA; V_{CC} = 2.3 V		-	-	0.31	V
		I_O = 3.1 mA; V_{CC} = 2.3 V		-	-	0.44	V
		I_O = 2.7 mA; V_{CC} = 3.0 V		-	-	0.31	V
		I_O = 4.0 mA; V_{CC} = 3.0 V		-	-	0.44	V
		X2 output; V_I = GND or V_{CC}					
		I_O = 20 μA; V_{CC} = 0.8 V to 3.6 V		-	-	0.1	V
		I_O = 1.1 mA; V_{CC} = 1.1 V		-	-	0.3 × V_{CC}	V
		I_O = 1.7 mA; V_{CC} = 1.4 V		-	-	0.31	V
		I_O = 1.9 mA; V_{CC} = 1.65 V		-	-	0.31	V
		I_O = 2.3 mA; V_{CC} = 2.3 V		-	-	0.31	V
		I_O = 3.1 mA; V_{CC} = 2.3 V		-	-	0.44	V
		I_O = 2.7 mA; V_{CC} = 3.0 V		-	-	0.31	V
		I_O = 4.0 mA; V_{CC} = 3.0 V		-	-	0.44	V
I_I	input leakage current	X1 input					
		V_I = $\overline{EN}$ = V_{CC}; V_{CC} = 0 V to 3.6 V		-	-	±0.1	μA
		$\overline{EN}$ input					
		V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V		-	-	±0.1	μA
I_{pu}	pull-up current	X1 input; $\overline{EN}$ = V_{CC}					
		V_I = GND; V_{CC} = 0.8 V to 3.6 V		-	-	15	μA
I_{OZ}	OFF-state output current	Y output; V_O = 0 V to 3.6 V; V_{CC} = 0 V to 3.6 V; $\overline{EN}$ = V_{CC}		-	-	±0.1	μA
I_{OFF}	power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V	[1]	-	-	±0.2	μA
ΔI_{OFF}	additional power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V to 0.2 V	[1]	-	-	±0.2	μA
I_{CC}	supply current	V_I = GND or V_{CC}; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V		-	-	75	μA
ΔI_{CC}	additional supply current	$\overline{EN}$ input					
		V_I = V_{CC} – 0.6 V; I_O = 0 A; V_{CC} = 3.3 V		-	-	40	μA
C_I	input capacitance	X1 input					
		V_{CC} = 0 V to 3.6 V; V_I = GND or V_{CC}		-	1.3	-	pF
		$\overline{EN}$ input					
		V_{CC} = 0 V to 3.6 V; V_I = GND or V_{CC}		-	0.8	-	pF

Table 7. Static characteristics *...continued*
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_O	output capacitance	X2 output				
		V_O = GND; V_{CC} = 0 V	-	1.5	-	pF
		Y output				
		V_O = GND; V_{CC} = 0 V	-	1.7	-	pF
g_{fs}	forward transconductance	see Figure 10 and Figure 11				
		V_{CC} = 0.8 V	-	-	-	mA/V
		V_{CC} = 1.1 V to 1.3 V	0.2	-	9.9	mA/V
		V_{CC} = 1.4 V to 1.6 V	3.9	-	17.7	mA/V
		V_{CC} = 1.65 V to 1.95 V	7.9	-	24.3	mA/V
		V_{CC} = 2.3 V to 2.7 V	18	-	30.7	mA/V
		V_{CC} = 3.0 V to 3.6 V	20.5	-	32.4	mA/V
R_{bias}	bias resistance	$\overline{EN}$ = GND; f_i = 0 Hz; V_I = 0 V or V_{CC}; See Figure 5; for frequency behavior see Figure 6	1.08	1.62	3.08	MΩ
T_{amb} = −40 °C to +85 °C						
V_{IH}	HIGH-level input voltage	X1 input				
		V_{CC} = 0.8 V to 3.6 V	0.75 × V_{CC}	-	-	V
		$\overline{EN}$ input				
		V_{CC} = 0.8 V	0.70 × V_{CC}	-	-	V
		V_{CC} = 0.9 V to 1.95 V	0.65 × V_{CC}	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V_{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	X1 input				
		V_{CC} = 0.8 V to 3.6 V	-	-	0.25 × V_{CC}	V
		$\overline{EN}$ input				
		V_{CC} = 0.8 V	-	-	0.30 × V_{CC}	V
		V_{CC} = 0.9 V to 1.95 V	-	-	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 3.0 V to 3.6 V	-	-	0.9	V

Table 7. Static characteristics *...continued*
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{OH}	HIGH-level output voltage	Y output; V_I at X1 input = V_{IH} or V_{IL}				
		I_O = −20 μA; V_{CC} = 0.8 V to 3.6 V	V_{CC} − 0.1	-	-	V
		I_O = −1.1 mA; V_{CC} = 1.1 V	0.7 × V_{CC}	-	-	V
		I_O = −1.7 mA; V_{CC} = 1.4 V	1.03	-	-	V
		I_O = −1.9 mA; V_{CC} = 1.65 V	1.30	-	-	V
		I_O = −2.3 mA; V_{CC} = 2.3 V	1.97	-	-	V
		I_O = −3.1 mA; V_{CC} = 2.3 V	1.85	-	-	V
		I_O = −2.7 mA; V_{CC} = 3.0 V	2.67	-	-	V
		I_O = −4.0 mA; V_{CC} = 3.0 V	2.55	-	-	V
		X2 output; V_I = GND or V_{CC}				
		I_O = −20 μA; V_{CC} = 0.8 V to 3.6 V	V_{CC} − 0.1	-	-	V
		I_O = −1.1 mA; V_{CC} = 1.1 V	0.7 × V_{CC}	-	-	V
		I_O = −1.7 mA; V_{CC} = 1.4 V	1.03	-	-	V
		I_O = −1.9 mA; V_{CC} = 1.65 V	1.30	-	-	V
		I_O = −2.3 mA; V_{CC} = 2.3 V	1.97	-	-	V
		I_O = −3.1 mA; V_{CC} = 2.3 V	1.85	-	-	V
		I_O = −2.7 mA; V_{CC} = 3.0 V	2.67	-	-	V
		I_O = −4.0 mA; V_{CC} = 3.0 V	2.55	-	-	V
V_{OL}	LOW-level output voltage	Y output; V_I at X1 input = V_{IH} or V_{IL}				
		I_O = 20 μA; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I_O = 1.1 mA; V_{CC} = 1.1 V	-	-	0.3 × V_{CC}	V
		I_O = 1.7 mA; V_{CC} = 1.4 V	-	-	0.37	V
		I_O = 1.9 mA; V_{CC} = 1.65 V	-	-	0.35	V
		I_O = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		I_O = 3.1 mA; V_{CC} = 2.3 V	-	-	0.45	V
		I_O = 2.7 mA; V_{CC} = 3.0 V	-	-	0.33	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.45	V
		X2 output; V_I = GND or V_{CC}				
		I_O = 20 μA; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I_O = 1.1 mA; V_{CC} = 1.1 V	-	-	0.3 × V_{CC}	V
		I_O = 1.7 mA; V_{CC} = 1.4 V	-	-	0.37	V
		I_O = 1.9 mA; V_{CC} = 1.65 V	-	-	0.35	V
		I_O = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		I_O = 3.1 mA; V_{CC} = 2.3 V	-	-	0.45	V
		I_O = 2.7 mA; V_{CC} = 3.0 V	-	-	0.33	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.45	V

Table 7. Static characteristics *...continued*
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_I	input leakage current	X1 input					
		$V_I = \overline{EN} = V_{CC}$; V_{CC} = 0 V to 3.6 V		-	-	±0.5	µA
		$\overline{EN}$ input					
		V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V		-	-	±0.5	µA
I_{pu}	pull-up current	X1 input; $\overline{EN} = V_{CC}$					
		V_I = GND; V_{CC} = 0.8 V to 3.6 V		-	-	15	µA
I_{OZ}	OFF-state output current	Y output; V_O = 0 V to 3.6 V; V_{CC} = 0 V to 3.6 V; $\overline{EN} = V_{CC}$		-	-	±0.5	µA
I_{OFF}	power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V	[1]	-	-	±0.5	µA
ΔI_{OFF}	additional power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V to 0.2 V	[1]	-	-	±0.6	µA
I_{CC}	supply current	V_I = GND or V_{CC}; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V		-	-	75	µA
ΔI_{CC}	additional supply current	$\overline{EN}$ input					
		$V_I = V_{CC} - 0.6$ V; I_O = 0 A; V_{CC} = 3.3 V		-	-	50	µA
g_{fs}	forward transconductance	see Figure 10 and Figure 11					
		V_{CC} = 0.8 V		-	-	-	mA/V
		V_{CC} = 1.1 V to 1.3 V		-	-	10.8	mA/V
		V_{CC} = 1.4 V to 1.6 V		1.8	-	21.2	mA/V
		V_{CC} = 1.65 V to 1.95 V		7.5	-	29.9	mA/V
		V_{CC} = 2.3 V to 2.7 V		15.0	-	38.0	mA/V
		V_{CC} = 3.0 V to 3.6 V		17.8	-	39.2	mA/V
R_{bias}	bias resistance	$\overline{EN}$ = GND; f_i = 0 Hz; V_I = 0 V or V_{CC}; See Figure 5; for frequency behavior see Figure 6		1.07	-	3.11	MΩ

Table 7. Static characteristics *...continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = −40 °C to +125 °C						
V_{IH}	HIGH-level input voltage	X1 input				
		V_{CC} = 0.8 V to 3.6 V	0.75 × V_{CC}	-	-	V
		$\overline{EN}$ input				
		V_{CC} = 0.8 V	0.75 × V_{CC}	-	-	V
		V_{CC} = 0.9 V to 1.95 V	0.70 × V_{CC}	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V_{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	X1 input				
		V_{CC} = 0.8 V to 3.6 V	-	-	0.25 × V_{CC}	V
		$\overline{EN}$ input				
		V_{CC} = 0.8 V	-	-	0.25 × V_{CC}	V
		V_{CC} = 0.9 V to 1.95 V	-	-	0.30 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	Y output; V_I at X1 input = V_{IH} or V_{IL}				
		I_O = −20 μA; V_{CC} = 0.8 V to 3.6 V	V_{CC} − 0.11	-	-	V
		I_O = −1.1 mA; V_{CC} = 1.1 V	0.6 × V_{CC}	-	-	V
		I_O = −1.7 mA; V_{CC} = 1.4 V	0.93	-	-	V
		I_O = −1.9 mA; V_{CC} = 1.65 V	1.17	-	-	V
		I_O = −2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		I_O = −3.1 mA; V_{CC} = 2.3 V	1.67	-	-	V
		I_O = −2.7 mA; V_{CC} = 3.0 V	2.40	-	-	V
		I_O = −4.0 mA; V_{CC} = 3.0 V	2.30	-	-	V
		X2 output; V_I = GND or V_{CC}				
		I_O = −20 μA; V_{CC} = 0.8 V to 3.6 V	V_{CC} − 0.11	-	-	V
		I_O = −1.1 mA; V_{CC} = 1.1 V	0.6 × V_{CC}	-	-	V
		I_O = −1.7 mA; V_{CC} = 1.4 V	0.93	-	-	V
		I_O = −1.9 mA; V_{CC} = 1.65 V	1.17	-	-	V
		I_O = −2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		I_O = −3.1 mA; V_{CC} = 2.3 V	1.67	-	-	V
		I_O = −2.7 mA; V_{CC} = 3.0 V	2.40	-	-	V
		I_O = −4.0 mA; V_{CC} = 3.0 V	2.30	-	-	V

Table 7. Static characteristics *...continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

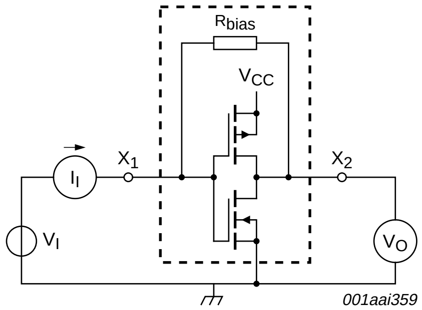
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{OL}	LOW-level output voltage	Y output; $V_I = V_{IH}$ or V_{IL}					
		$I_O = 20$ µA; $V_{CC} = 0.8$ V to 3.6 V		-	-	0.11	V
		$I_O = 1.1$ mA; $V_{CC} = 1.1$ V		-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7$ mA; $V_{CC} = 1.4$ V		-	-	0.41	V
		$I_O = 1.9$ mA; $V_{CC} = 1.65$ V		-	-	0.39	V
		$I_O = 2.3$ mA; $V_{CC} = 2.3$ V		-	-	0.36	V
		$I_O = 3.1$ mA; $V_{CC} = 2.3$ V		-	-	0.50	V
		$I_O = 2.7$ mA; $V_{CC} = 3.0$ V		-	-	0.36	V
		$I_O = 4.0$ mA; $V_{CC} = 3.0$ V		-	-	0.50	V
		X2 output; V_I = GND or V_{CC}					
		$I_O = 20$ µA; $V_{CC} = 0.8$ V to 3.6 V		-	-	0.11	V
		$I_O = 1.1$ mA; $V_{CC} = 1.1$ V		-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7$ mA; $V_{CC} = 1.4$ V		-	-	0.41	V
		$I_O = 1.9$ mA; $V_{CC} = 1.65$ V		-	-	0.39	V
		$I_O = 2.3$ mA; $V_{CC} = 2.3$ V		-	-	0.36	V
		$I_O = 3.1$ mA; $V_{CC} = 2.3$ V		-	-	0.50	V
		$I_O = 2.7$ mA; $V_{CC} = 3.0$ V		-	-	0.36	V
		$I_O = 4.0$ mA; $V_{CC} = 3.0$ V		-	-	0.50	V
I_I	input leakage current	X1 input					
		$V_I = \overline{EN} = V_{CC}$; $V_{CC} = 0$ V to 3.6 V		-	-	±0.75	µA
		$\overline{EN}$ input					
		V_I = GND to 3.6 V; $V_{CC} = 0$ V to 3.6 V		-	-	±0.75	µA
I_{pu}	pull-up current	X1 input; $\overline{EN} = V_{CC}$					
		V_I = GND; $V_{CC} = 0.8$ V to 3.6 V		-	-	15	µA
I_{OZ}	OFF-state output current	Y output; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V; $\overline{EN} = V_{CC}$		-	-	±0.75	µA
I_{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	[1]	-	-	±0.75	µA
ΔI_{OFF}	additional power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	[1]	-	-	±0.75	µA
I_{CC}	supply current	V_I = GND or V_{CC}; $I_O = 0$ A; $V_{CC} = 0.8$ V to 3.6 V		-	-	75	µA
ΔI_{CC}	additional supply current	$\overline{EN}$ input					
		$V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V		-	-	75	µA

Table 7. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

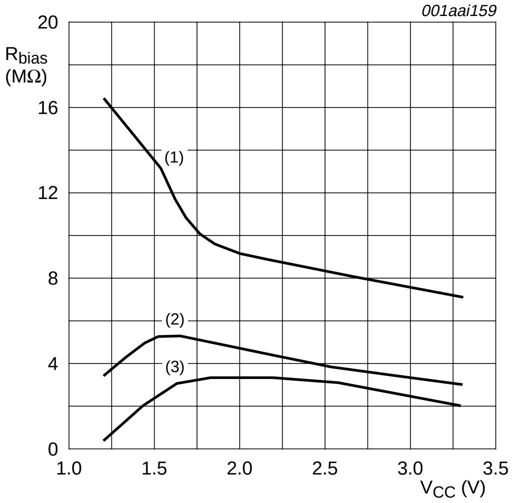
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
g_{fs}	forward transconductance	see Figure 10 and Figure 11				
		V_{CC} = 0.8 V	-	-	-	mA/V
		V_{CC} = 1.1 V to 1.3 V	-	-	10.8	mA/V
		V_{CC} = 1.4 V to 1.6 V	1.8	-	21.2	mA/V
		V_{CC} = 1.65 V to 1.95 V	6.9	-	29.9	mA/V
		V_{CC} = 2.3 V to 2.7 V	13.4	-	38.0	mA/V
		V_{CC} = 3.0 V to 3.6 V	15.8	-	39.2	mA/V
R_{bias}	bias resistance	$\overline{EN}$ = GND; f_i = 0 Hz; V_I = 0 V or V_{CC}; See Figure 5; for frequency behavior see Figure 6	1.07	-	3.11	MΩ

[1] Only for output Y and input $\overline{EN}$.



$$R_{bias} = \left|\frac{V_O - V_I}{I_I}\right|$$

Fig 5. Test circuit for measuring bias resistance



(1) f_i = 30 kHz.

(2) f_i = 1 MHz.

(3) f_i = 10 MHz.

Fig 6. Typical bias resistance versus supply voltage

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C			−40 °C to +125 °C			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C_L = 5 pF										
t_{pd}	propagation delay	X1 to X2; see Figure 7	[2]							
		V_{CC} = 0.8 V		-	6.2	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		0.9	2.3	4.4	0.9	4.8	5.3	ns
		V_{CC} = 1.4 V to 1.6 V		0.7	1.7	3.1	0.6	3.4	3.8	ns
		V_{CC} = 1.65 V to 1.95 V		0.5	1.4	2.6	0.5	2.9	3.2	ns
		V_{CC} = 2.3 V to 2.7 V		0.4	1.1	2.0	0.4	2.3	2.6	ns
		V_{CC} = 3.0 V to 3.6 V		0.3	1.0	1.8	0.3	2.1	2.4	ns
		X1 to Y; see Figure 7	[2]							
		V_{CC} = 0.8 V		-	18.5	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		2.8	5.9	12.5	3.2	14.8	16.3	ns
		V_{CC} = 1.4 V to 1.6 V		2.2	4.2	7.7	2.6	9.1	10.1	ns
		V_{CC} = 1.65 V to 1.95 V		1.9	3.5	6.2	2.2	7.8	8.6	ns
		V_{CC} = 2.3 V to 2.7 V		1.6	2.9	4.8	1.9	6.2	6.9	ns
		V_{CC} = 3.0 V to 3.6 V		1.4	2.6	4.1	1.7	4.7	5.2	ns
t_{en}	enable time	$\overline{EN}$ to Y; see Figure 8	[3]							
		V_{CC} = 0.8 V		-	31.2	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		3.1	6.1	13.8	2.9	16.3	18.0	ns
		V_{CC} = 1.4 V to 1.6 V		2.5	4.3	8.2	2.3	9.7	10.7	ns
		V_{CC} = 1.65 V to 1.95 V		2.1	3.6	6.5	2.0	7.6	8.4	ns
		V_{CC} = 2.3 V to 2.7 V		1.8	2.9	4.8	1.7	5.8	6.4	ns
		V_{CC} = 3.0 V to 3.6 V		1.7	2.6	4.1	1.7	4.7	5.2	ns
t_{dis}	disable time	$\overline{EN}$ to Y; see Figure 8	[4]							
		V_{CC} = 0.8 V		-	11.1	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		2.5	4.5	9.0	2.9	9.4	10.4	ns
		V_{CC} = 1.4 V to 1.6 V		2.0	3.3	6.4	2.3	6.7	7.4	ns
		V_{CC} = 1.65 V to 1.95 V		1.9	3.2	6.0	2.0	6.4	7.1	ns
		V_{CC} = 2.3 V to 2.7 V		1.4	2.3	4.4	1.7	4.7	5.2	ns
		V_{CC} = 3.0 V to 3.6 V		1.7	2.6	4.4	1.7	4.9	5.4	ns

Table 8. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C			−40 °C to +125 °C			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C_L = 10 pF										
t_{pd}	propagation delay	X1 to X2; see Figure 7	[2]							
		V_{CC} = 0.8 V		-	9.6	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		1.2	3.1	6.1	1.2	6.8	7.5	ns
		V_{CC} = 1.4 V to 1.6 V		1.0	2.3	4.0	0.9	4.6	5.1	ns
		V_{CC} = 1.65 V to 1.95 V		0.8	1.9	3.3	0.7	3.8	4.2	ns
		V_{CC} = 2.3 V to 2.7 V		0.6	1.5	2.7	0.6	3.1	3.5	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	1.3	2.4	0.5	2.7	3.0	ns
		X1 to Y; see Figure 7	[2]							
		V_{CC} = 0.8 V		-	21.4	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		3.2	6.7	14.3	3.6	16.2	17.9	ns
		V_{CC} = 1.4 V to 1.6 V		2.1	4.9	8.9	3.0	10.1	11.2	ns
		V_{CC} = 1.65 V to 1.95 V		1.9	4.1	6.9	2.6	8.0	8.8	ns
		V_{CC} = 2.3 V to 2.7 V		2.1	3.4	5.4	2.3	6.6	7.3	ns
		V_{CC} = 3.0 V to 3.6 V		1.8	3.1	4.8	2.1	5.6	6.2	ns
t_{en}	enable time	$\overline{EN}$ to Y; see Figure 8	[3]							
		V_{CC} = 0.8 V		-	34.4	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		3.6	6.9	15.5	3.4	16.0	17.6	ns
		V_{CC} = 1.4 V to 1.6 V		2.3	5.0	9.3	2.2	9.6	10.6	ns
		V_{CC} = 1.65 V to 1.95 V		2.0	4.2	7.2	1.9	7.9	8.7	ns
		V_{CC} = 2.3 V to 2.7 V		1.8	3.4	5.5	1.7	6.4	7.1	ns
		V_{CC} = 3.0 V to 3.6 V		1.7	3.2	4.9	1.7	5.5	6.1	ns
t_{dis}	disable time	$\overline{EN}$ to Y; see Figure 8	[4]							
		V_{CC} = 0.8 V		-	13.0	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		3.4	5.7	10.4	3.4	10.8	11.9	ns
		V_{CC} = 1.4 V to 1.6 V		2.1	4.2	7.6	2.2	8.0	8.8	ns
		V_{CC} = 1.65 V to 1.95 V		2.2	4.3	7.3	1.9	7.6	8.4	ns
		V_{CC} = 2.3 V to 2.7 V		1.6	3.1	5.3	1.7	5.5	6.1	ns
		V_{CC} = 3.0 V to 3.6 V		2.1	3.8	6.0	1.7	6.5	7.2	ns

Table 8. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C			−40 °C to +125 °C			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C_L = 15 pF										
t_{pd}	propagation delay	X1 to X2; see Figure 7	[2]							
		V_{CC} = 0.8 V		-	13.0	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		1.6	3.8	7.9	1.4	8.8	9.7	ns
		V_{CC} = 1.4 V to 1.6 V		1.3	2.8	4.9	1.1	5.7	6.3	ns
		V_{CC} = 1.65 V to 1.95 V		1.0	2.3	4.0	0.9	4.7	5.2	ns
		V_{CC} = 2.3 V to 2.7 V		0.8	1.9	3.2	0.8	3.7	4.1	ns
		V_{CC} = 3.0 V to 3.6 V		0.7	1.6	2.9	0.7	3.3	3.7	ns
		X1 to Y; see Figure 7	[2]							
		V_{CC} = 0.8 V		-	24.2	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		3.6	7.5	16.1	4.0	17.6	19.4	ns
		V_{CC} = 1.4 V to 1.6 V		3.0	5.4	9.7	3.3	10.6	11.7	ns
		V_{CC} = 1.65 V to 1.95 V		2.2	4.6	7.7	2.9	9.0	9.9	ns
		V_{CC} = 2.3 V to 2.7 V		2.0	3.9	6.1	2.6	7.3	8.1	ns
		V_{CC} = 3.0 V to 3.6 V		2.0	3.6	5.4	2.3	5.9	6.5	ns
t_{en}	enable time	$\overline{EN}$ to Y; see Figure 8	[3]							
		V_{CC} = 0.8 V		-	37.5	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		4.0	7.7	17.2	3.7	17.5	19.3	ns
		V_{CC} = 1.4 V to 1.6 V		3.0	5.5	10.0	2.5	10.2	11.3	ns
		V_{CC} = 1.65 V to 1.95 V		2.3	4.7	7.9	2.1	9.2	10.2	ns
		V_{CC} = 2.3 V to 2.7 V		2.0	3.9	6.2	2.0	7.4	8.2	ns
		V_{CC} = 3.0 V to 3.6 V		2.0	3.6	5.5	1.9	6.0	6.6	ns
t_{dis}	disable time	$\overline{EN}$ to Y; see Figure 8	[4]							
		V_{CC} = 0.8 V		-	14.8	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		4.3	6.8	11.2	3.7	12.4	13.7	ns
		V_{CC} = 1.4 V to 1.6 V		3.0	5.1	8.1	2.5	8.9	9.8	ns
		V_{CC} = 1.65 V to 1.95 V		3.0	5.4	8.0	2.1	9.3	10.3	ns
		V_{CC} = 2.3 V to 2.7 V		2.1	3.9	6.1	2.0	7.3	8.1	ns
		V_{CC} = 3.0 V to 3.6 V		2.9	5.1	7.2	1.9	7.9	8.7	ns

Table 8. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C			−40 °C to +125 °C			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C_L = 30 pF										
t_{pd}	propagation delay	X1 to X2; see Figure 7	[2]							
		V_{CC} = 0.8 V		-	23.2	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		2.4	6.0	13.1	2.2	14.8	16.3	ns
		V_{CC} = 1.4 V to 1.6 V		2.0	4.2	7.6	1.8	9.0	9.9	ns
		V_{CC} = 1.65 V to 1.95 V		1.7	3.6	6.1	1.5	7.2	8.0	ns
		V_{CC} = 2.3 V to 2.7 V		1.4	2.9	4.8	1.3	5.7	6.3	ns
		V_{CC} = 3.0 V to 3.6 V		1.2	2.5	4.3	1.1	5.1	5.7	ns
		X1 to Y; see Figure 7	[2]							
		V_{CC} = 0.8 V		-	32.6	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		4.8	9.6	21.0	5.0	21.7	23.9	ns
		V_{CC} = 1.4 V to 1.6 V		4.0	6.9	12.4	4.3	13.5	14.9	ns
		V_{CC} = 1.65 V to 1.95 V		2.9	5.9	9.8	3.8	10.7	11.8	ns
		V_{CC} = 2.3 V to 2.7 V		2.7	5.0	7.5	3.3	8.2	9.1	ns
		V_{CC} = 3.0 V to 3.6 V		2.7	4.7	6.8	3.1	7.7	8.5	ns
t_{en}	enable time	$\overline{EN}$ to Y; see Figure 8	[3]							
		V_{CC} = 0.8 V		-	47.1	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		5.2	9.9	21.0	4.8	21.7	23.9	ns
		V_{CC} = 1.4 V to 1.6 V		4.0	7.1	12.4	3.1	13.5	14.9	ns
		V_{CC} = 1.65 V to 1.95 V		3.0	6.0	9.9	2.8	10.7	11.8	ns
		V_{CC} = 2.3 V to 2.7 V		2.7	5.0	7.7	2.6	8.1	9.0	ns
		V_{CC} = 3.0 V to 3.6 V		2.7	4.8	6.8	2.6	7.7	8.5	ns
t_{dis}	disable time	$\overline{EN}$ to Y; see Figure 8	[4]							
		V_{CC} = 0.8 V		-	20.3	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		6.0	10.2	15.3	4.8	16.5	18.2	ns
		V_{CC} = 1.4 V to 1.6 V		4.4	7.8	11.2	3.1	12.3	13.6	ns
		V_{CC} = 1.65 V to 1.95 V		5.1	8.8	12.5	2.8	13.3	14.7	ns
		V_{CC} = 2.3 V to 2.7 V		3.6	6.3	8.6	2.6	9.5	10.5	ns
		V_{CC} = 3.0 V to 3.6 V		5.2	8.8	11.5	2.6	13.0	14.3	ns

Table 8. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C_L = 5 pF, 10 pF, 15 pF and 30 pF										
C_{PD}	power dissipation capacitance	f_i = 1 MHz; $\overline{EN}$ = GND; V_I = GND to V_{CC}	[5][6]							
		V_{CC} = 0.8 V		-	7.1	-	-	-	-	pF
		V_{CC} = 1.1 V to 1.3 V		-	12.9	-	-	-	-	pF
		V_{CC} = 1.4 V to 1.6 V		-	19.2	-	-	-	-	pF
		V_{CC} = 1.65 V to 1.95 V		-	19.9	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V		-	21.6	-	-	-	-	pF
		V_{CC} = 3.0 V to 3.6 V		-	24.3	-	-	-	-	pF

[1] All typical values are measured at nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] t_{en} is the same as t_{PZH} and t_{PZL}.

[4] t_{dis} is the same as t_{PHZ} and t_{PLZ}.

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

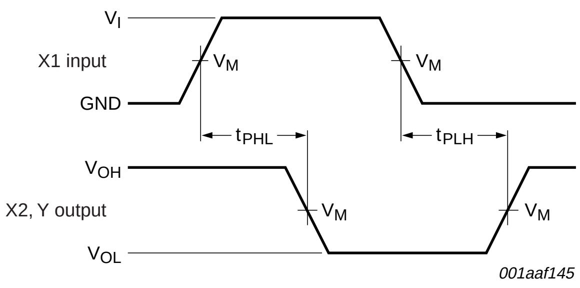
V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

[6] Feedback current is included in C_{PD}.

12. Waveforms



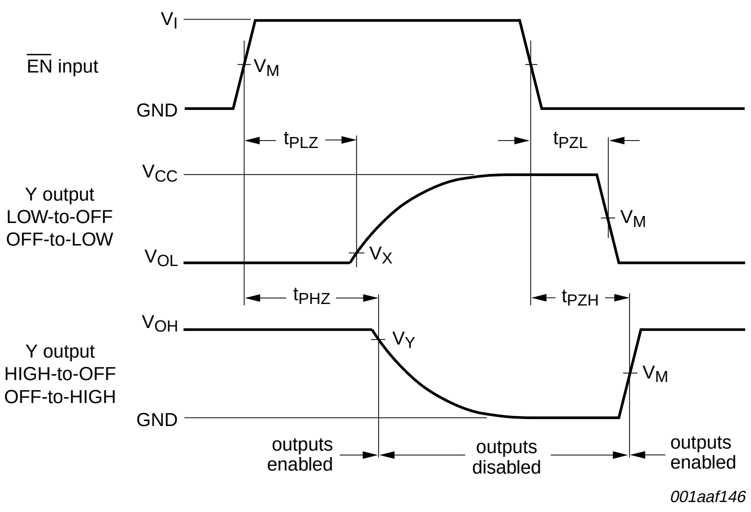
Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 7. The input (X1) to output (X2, Y) propagation delays

Table 9. Measurement points

Supply voltage	Output	Input		
V_{CC}	V_M	V_M	V_I	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{CC}	≤ 3.0 ns



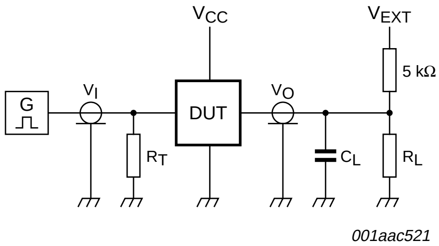
Measurement points are given in Table 10.

Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 8. Enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output		
V_{CC}	V_M	V_M	V_X	V_Y
0.8 V to 1.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{OL} + 0.1 V	V_{OH} − 0.1 V
1.65 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{OL} + 0.15 V	V_{OH} − 0.15 V
3.0 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{OL} + 0.3 V	V_{OH} − 0.3 V



Test data is given in Table 11.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

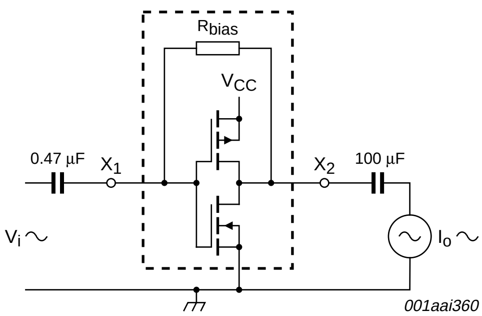
V_{EXT} = External voltage for measuring switching times.

Fig 9. Load circuitry for switching times

Table 11. Test data

Supply voltage	Load		V_{EXT}		
V_{CC}	C_L	R_L [1]	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times R_L = 5 kΩ, for measuring propagation delays, setup and hold times and pulse width R_L = 1 MΩ.

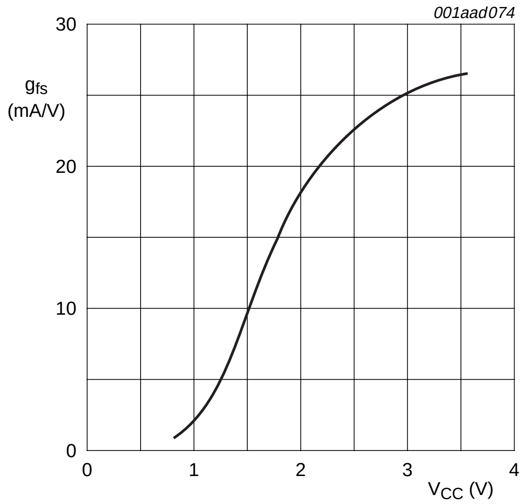


$$g_{fs} = \frac{\Delta I_O}{\Delta V_I}$$

f_i = 1 kHz.

V_O is constant.

Fig 10. Test set-up for measuring forward transconductance



T_{amb} = 25 °C.

Fig 11. Typical forward transconductance as a function of supply voltage

13. Application information

Crystal controlled oscillator circuits are widely used in clock pulse generators because of their excellent frequency stability and wide operating frequency range. The use of the 74AUP1Z125 provides the additional advantages of low power dissipation, stable operation over a wide range of frequency and temperature and a very small footprint. This application information describes crystal characteristics, design and testing of crystal oscillator circuits based on the 74AUP1Z125.

13.1 Crystal characteristics

Figure 12 is the equivalent circuit of a quartz crystal.

The reactive and resistive component of the impedance of the crystal alone and the crystal with a series and a parallel capacitance is shown in Figure 13.

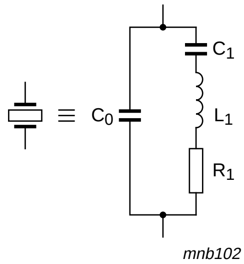
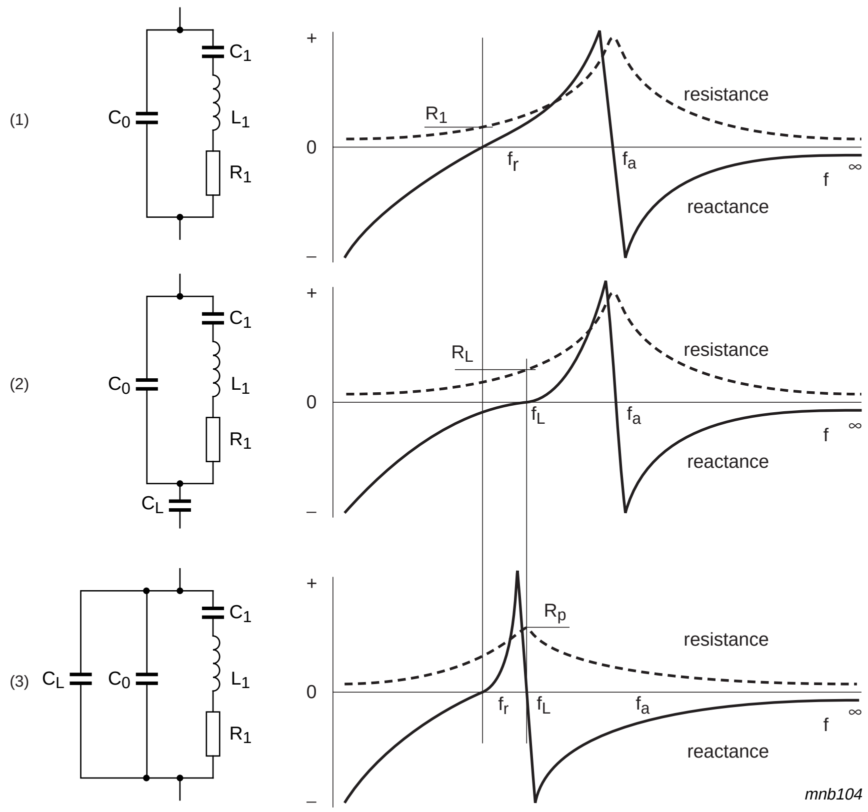


Fig 12. Equivalent circuit of a crystal



(1) (a) = resonance

(2) (b) = anti-resonance

(3) (c) = load resonance

Fig 13. Reactance and resistance characteristics of a crystal

13.1.1 Design

Figure 14 shows the recommended way to connect a crystal to the 74AUP1Z125. This circuit is basically a Pierce oscillator circuit in which the crystal is operating at its fundamental frequency and is tuned by the parallel load capacitance of C_1 and C_2. C_1 and C_2 are in series with the crystal. They should be approximately equal. R_1 is the drive-limiting resistor and is set to approximately the same value as the reactance of C_1 at the crystal frequency ($R_1 = X_{C1}$). This will result in an input to the crystal of 50 % of the rail-to-rail output of X2. This keeps the drive level into the crystal within drive specifications (the designer should verify this). Overdriving the crystal can cause damage.

The internal bias resistor provides negative feedback and sets a bias point of the inverter near mid-supply, operating the 74AUP1GU04 in the high gain linear region.

To calculate the values of C_1 and C_2, the designer can use the formula:

$$C_L = \frac{C_1 \times C_2}{C_1 + C_2} + C_s$$

C_L is the load capacitance as specified by the crystal manufacturer, C_s is the stray capacitance of the circuit (for the 74AUP1Z125 this is equal to an input capacitance of 1.5 pF).

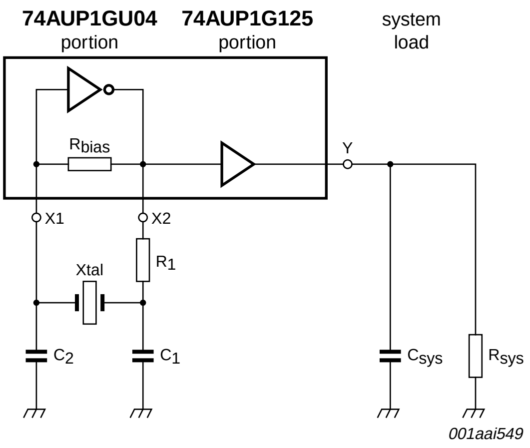


Fig 14. Crystal oscillator configuration

13.1.2 Testing

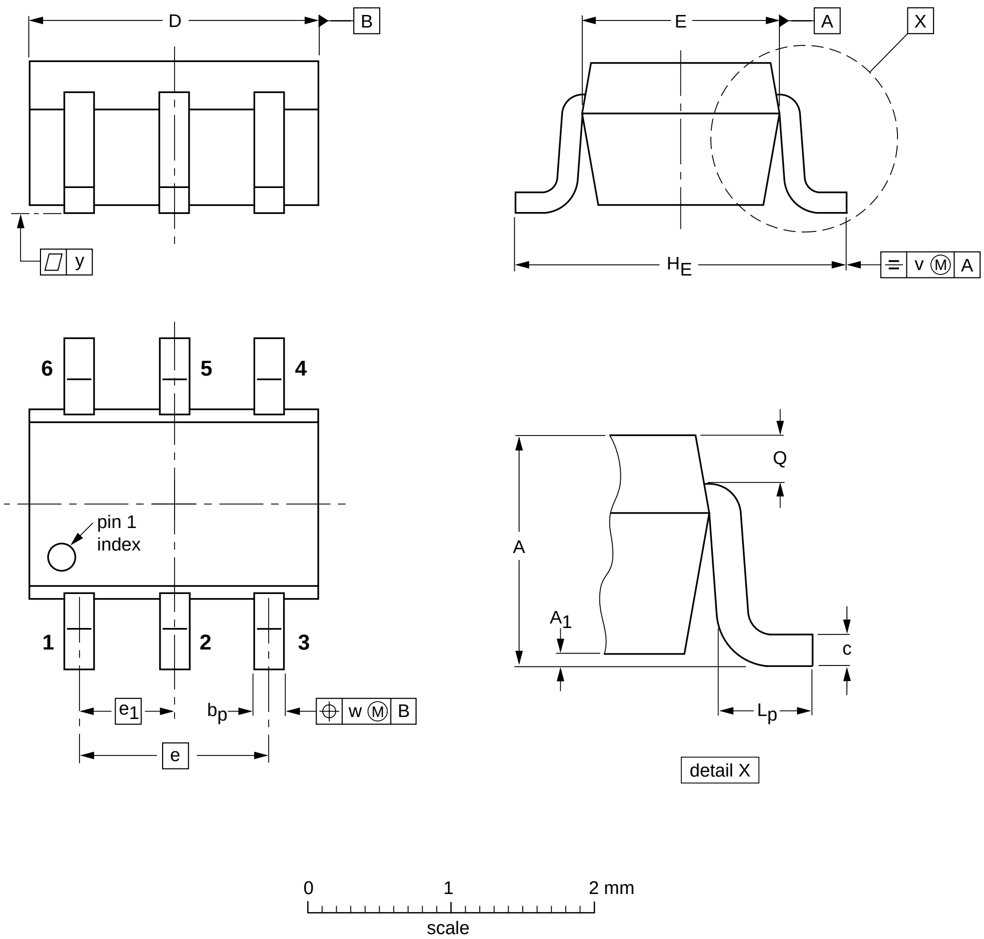
After the calculations are performed for a particular crystal, the oscillator circuit should be tested. The following simple checks will verify the prototype design of a crystal controlled oscillator circuit. Perform them after laying out the board:

- Test the oscillator over worst-case conditions (lowest supply voltage, worst-case crystal and highest operating temperature). Adding series and parallel resistors can simulate a worse case crystal.
- Insure that the circuit does not oscillate without the crystal.
- Check the frequency stability over a supply range greater than that which is likely to occur during normal operation.
- Check that the start-up time is within system requirements.

As the 74AUP1Z125 isolates the system loading, once the design is optimized, the single layout may work in multiple applications for any given crystal.

14. Package outline

Plastic surface-mounted package; 6 leads **SOT363**



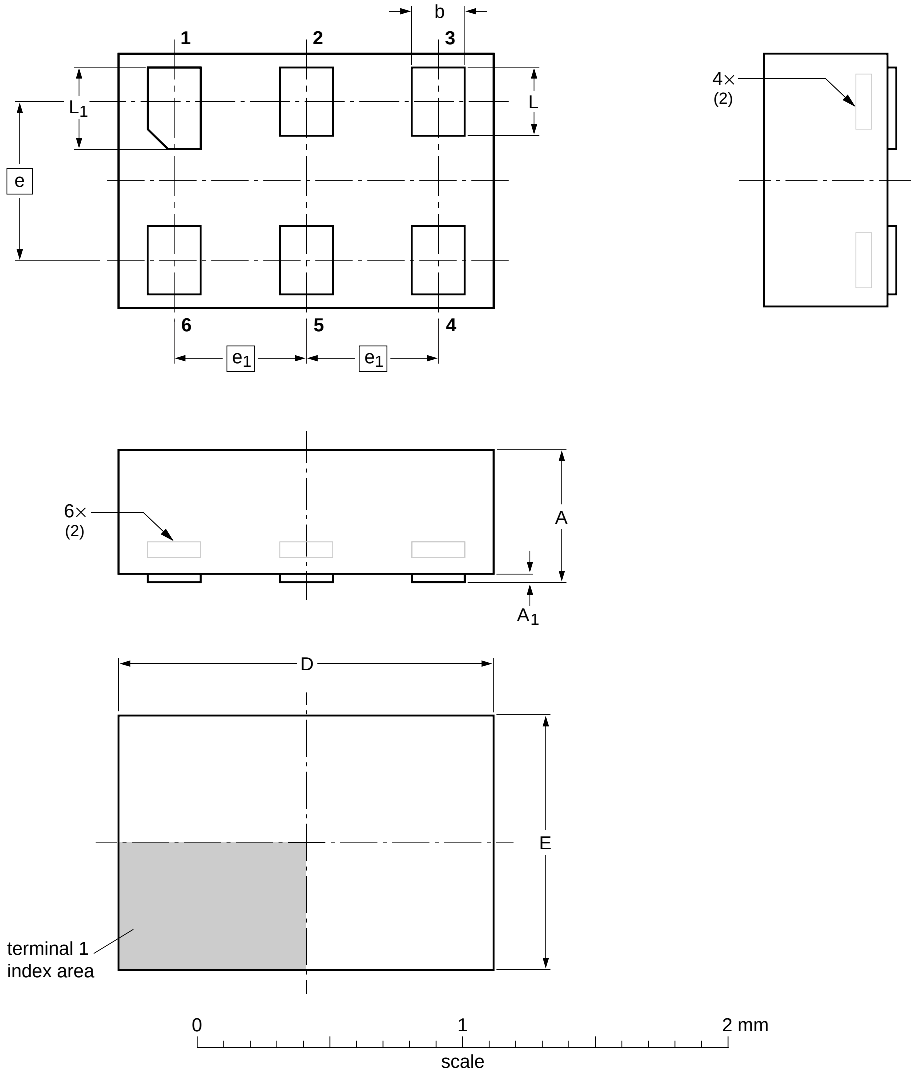
DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT363			SC-88			~~04-11-08~~ 06-03-16

Fig 15. Package outline SOT363 (SC-88)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm **SOT886**



DIMENSIONS (mm are the original dimensions)

UNIT	$A^{(1)}$ max	A_1 max	b	D	E	e	e_1	L	L_1
mm	0.5	0.04	0.25 0.17	1.5 1.4	1.05 0.95	0.6	0.5	0.35 0.27	0.40 0.32

Notes

1. Including plating thickness.
2. Can be visible in some manufacturing processes.

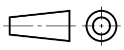
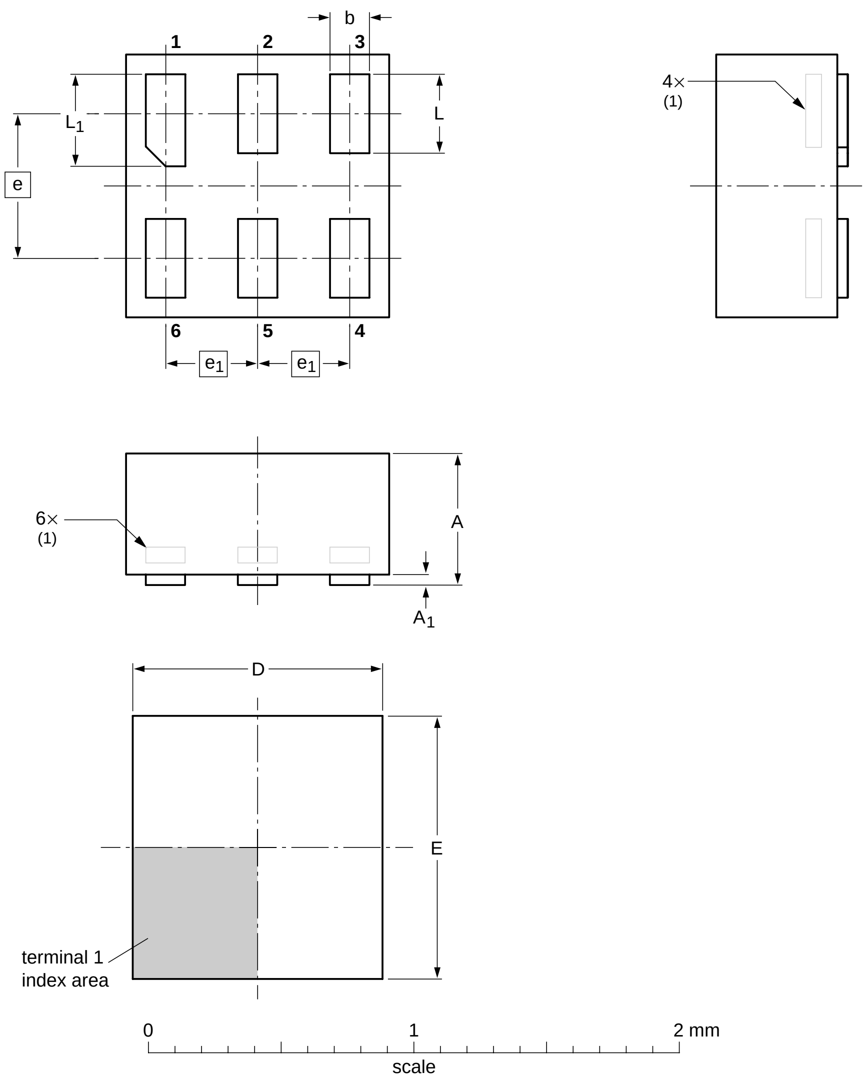
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT886		MO-252				~~04-07-15~~ 04-07-22

Fig 16. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm **SOT891**



DIMENSIONS (mm are the original dimensions)

UNIT	A max	A_1 max	b	D	E	e	e_1	L	L_1
mm	0.5	0.04	0.20 0.12	1.05 0.95	1.05 0.95	0.55	0.35	0.35 0.27	0.40 0.32

Note

1. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT891						~~05-04-06~~ 07-05-15

Fig 17. Package outline SOT891 (XSON6)

15. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

16. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1Z125_2	20080807	Product data sheet	-	74AUP1Z125_1
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Section 2 “Features”: Removed: Low static power consumption; I_{CC} 0.9 µA maximum. • Section 10 “Static characteristics”: Removed: Feedback current (I_{fbck}). Changed: Maximum supply current (I_{CC}). Added: forward transconductance and bias resistance. • Section 11 “Dynamic characteristics”: Changed: Typical power dissipation capacitance.			
74AUP1Z125_1	20060803	Product data sheet	-	-

17. Legal information

17.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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